

Description

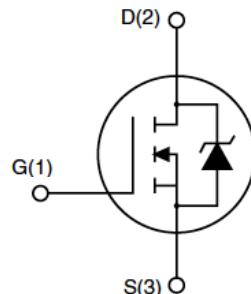
Features		
V _{DSS}	R _{DSON} @ 10V (typ)	I _D
200V	0.21Ω	9A
<ul style="list-style-type: none"> Fast switching 100% avalanche tested Improved dv/dt capability 		
Application		
<ul style="list-style-type: none"> DC Motor Control and Class D Amplifier Uninterruptible Power Supply (UPS) Automotive 		



TO-252



TO-251



Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Max.	Units
		TO-251/TO-252	
V _{DSS}	Drain-Source Voltage	200	V
V _{GSS}	Gate-Source Voltage	± 30	V
I _D	Continuous Drain Current	9	A
		5.83	A
I _{DM}	Pulsed Drain Current ^{note1}	36	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	320	mJ
dv/dt	Peak Diode Recovery Energy ^{note3}	5	V/ns
P _D	Power Dissipation $T_c = 25^\circ\text{C}$	83	W
	Linear Derating Factor $T_c > 25^\circ\text{C}$	0.67	W/°C
R _{θJC}	Thermal Resistance, Junction to Case	1.5	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C

*Drain current limited by maximum junction temperature

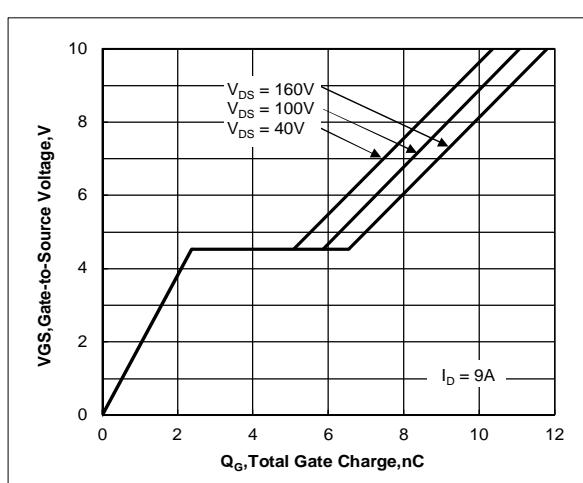
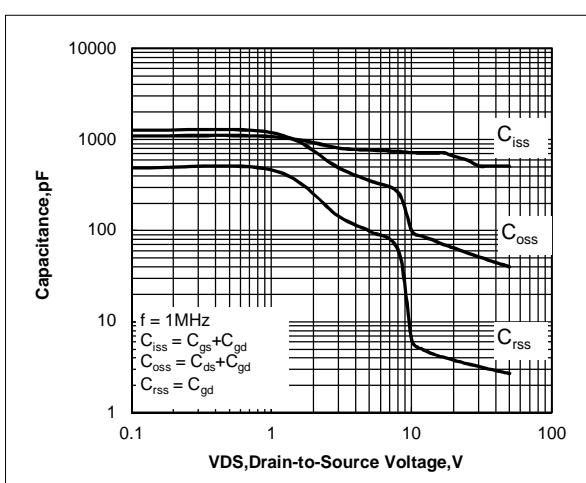
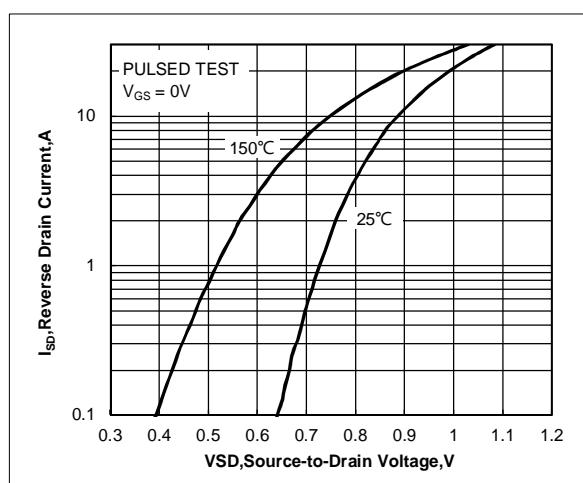
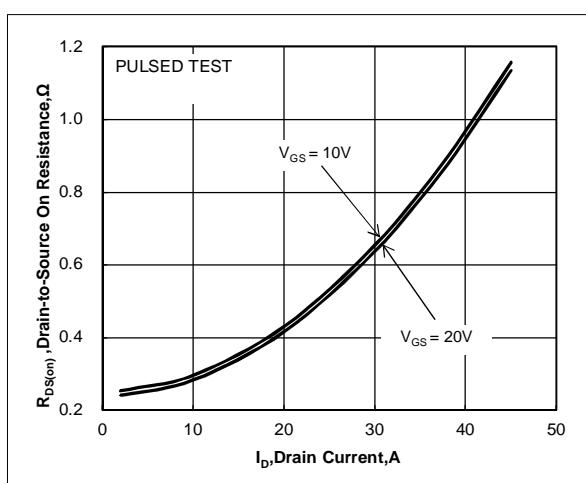
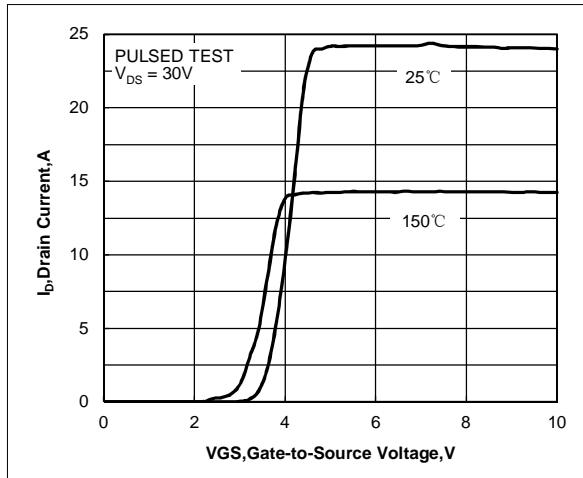
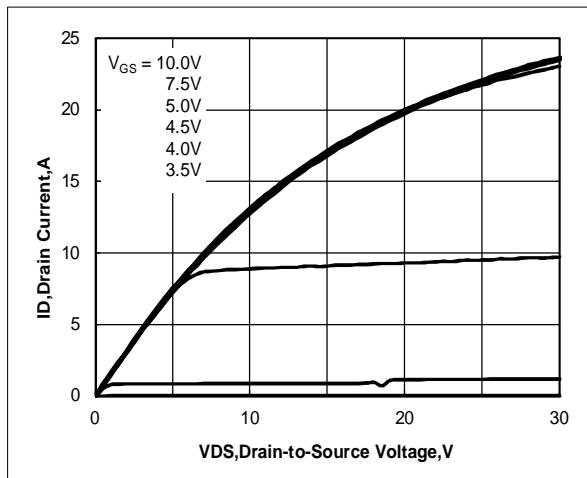
Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	200	-	-	V
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D = 250\mu\text{A}$	-	0.25	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 200V, V_{GS} = 0V$	-	-	1	μA
		$V_{DS} = 160V, T_C = 125^\circ\text{C}$	-	-	10	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage ^{note4}	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2	-	4	V
$R_{DS(\text{on})}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 4.5\text{A}$	-	0.21	0.25	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 30V, I_D = 4.5\text{A}$	-	9.2	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{MHz}$	-	509	-	pF
C_{oss}	Output Capacitance		-	51.5	-	pF
C_{rss}	Reverse Transfer Capacitance		-	3.2	-	pF
Q_g	Total Gate Charge	$V_{DD} = 160V, ID = 9A, V_{GS} = 10V$	-	11.8	-	nC
Q_{gs}	Gate-Source Charge		-	2.36	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3.98	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100V, I_D = 9A, R_G = 10\Omega, V_{GS} = 10V$	-	10.33	-	ns
t_r	Turn-On Rise Time		-	10.7	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	29.1	-	ns
t_f	Turn-Off Fall Time		-	11.1	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	9	-	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	36	-	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 9A$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_F = 9A, di/dt = 100A/\mu\text{s}$	-	201	-	ns
Q_{rr}	Reverse Recovery Charge		-	663	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 10mH, $I_{AS} = 8A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 9A$, $di/dt \leq 200A/\mu\text{s}$, $V_{DD} \leq B_{VDSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical Performance Characteristics



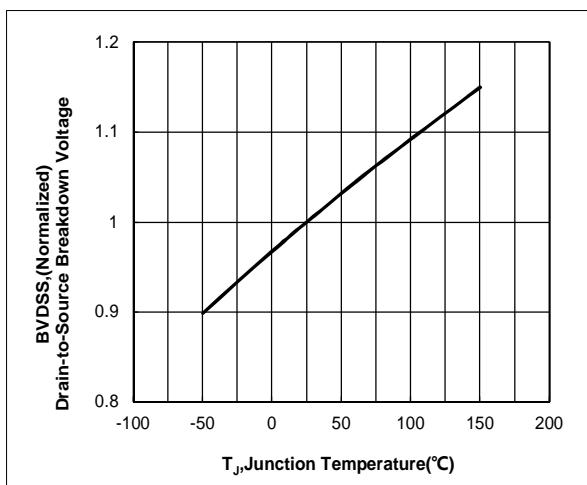


Figure 7. Normalized Breakdown Voltage vs.
Junction Temperature

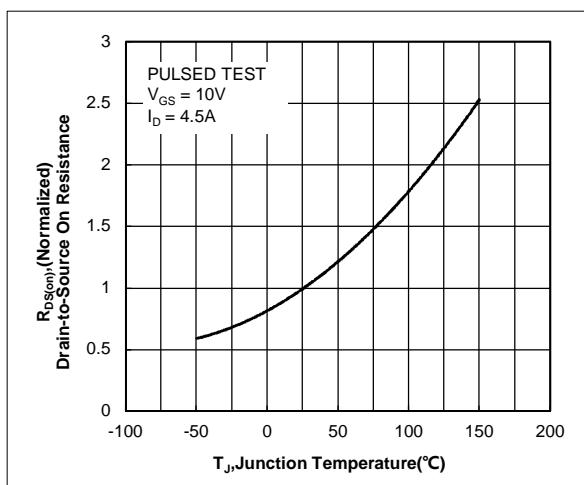


Figure 8. Normalized On Resistance vs.
Junction Temperature

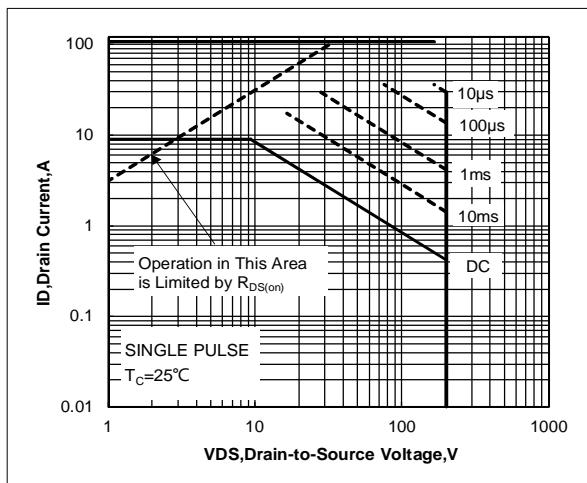


Figure 9. Maximum Safe Operating Area for RU9N20A

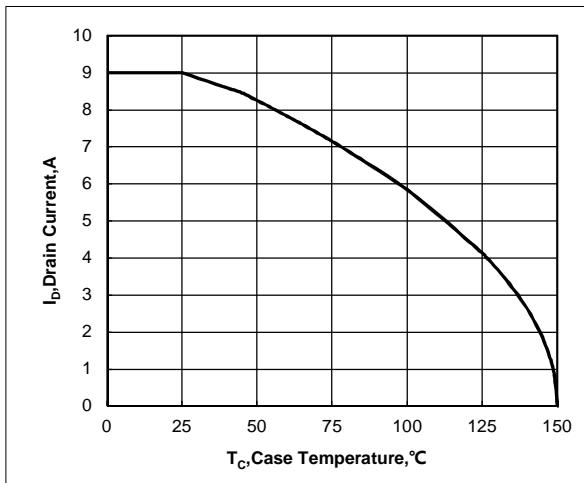


Figure 10. Maximum Continuous Drain Current vs.
Case Temperature

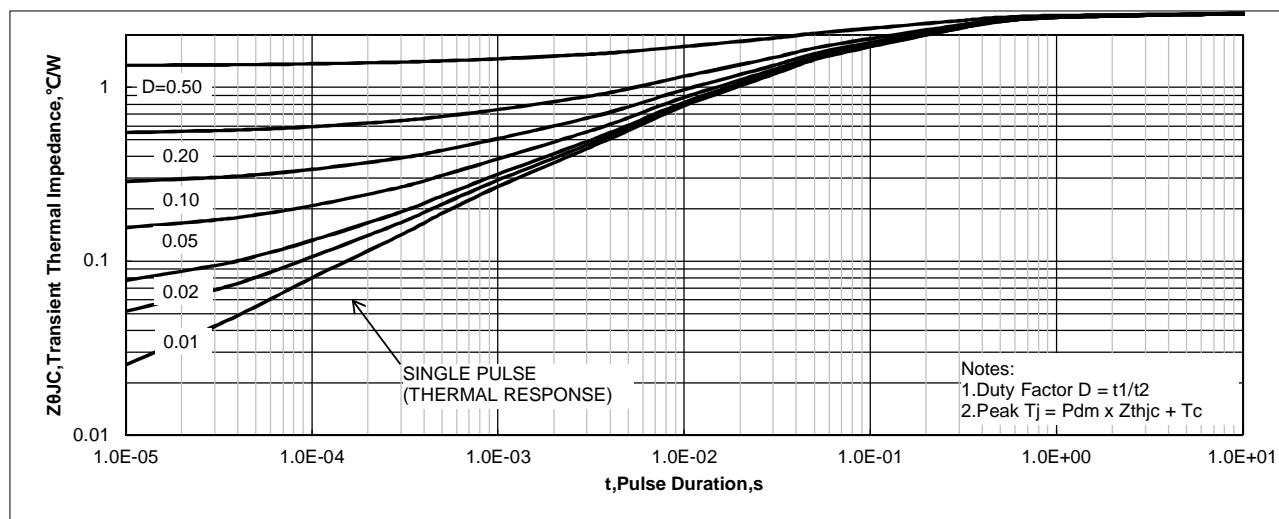


Figure 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case for RU9N20A

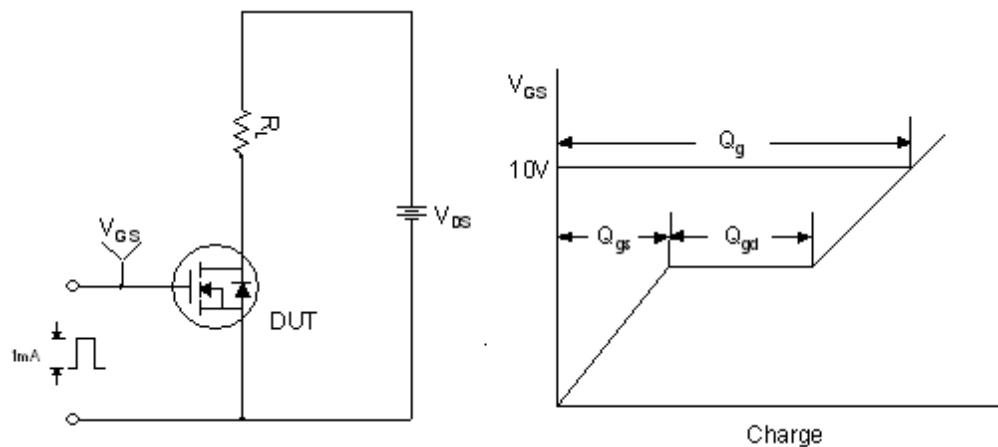


Figure 12. Gate Charge Test Circuit & Waveform

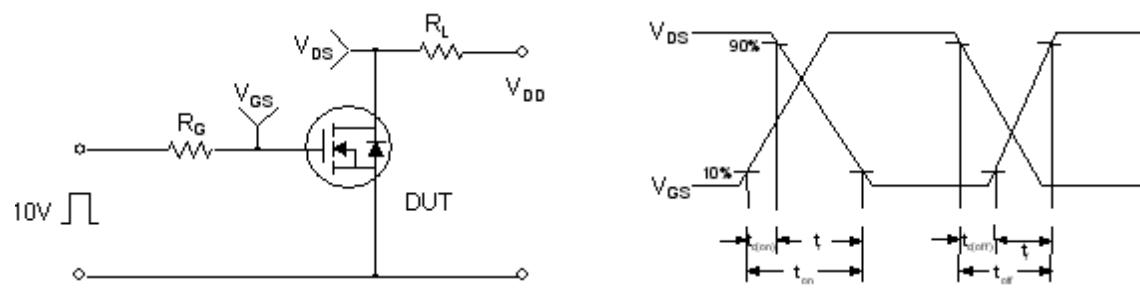


Figure 13. Resistive Switching Test Circuit & Waveforms

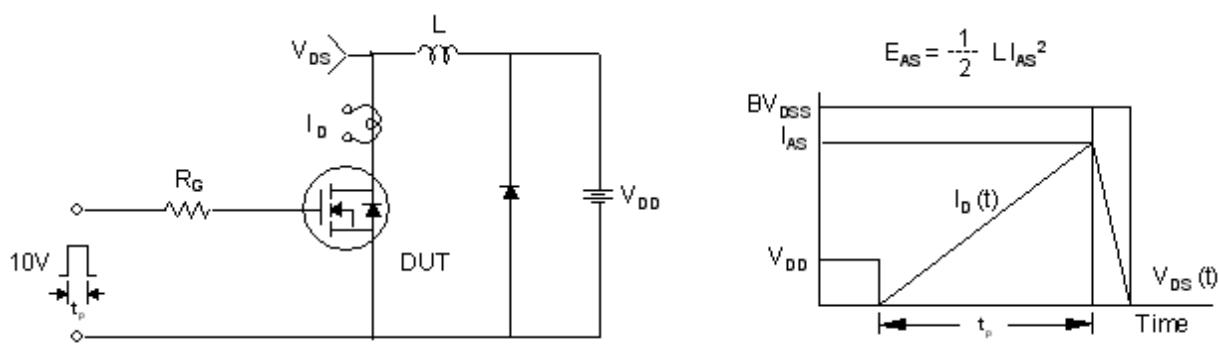
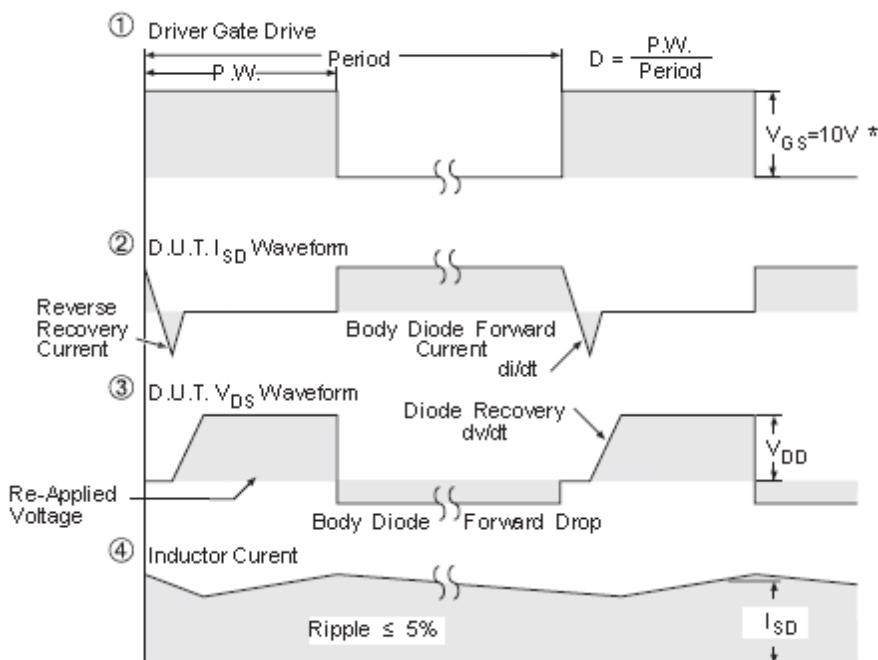
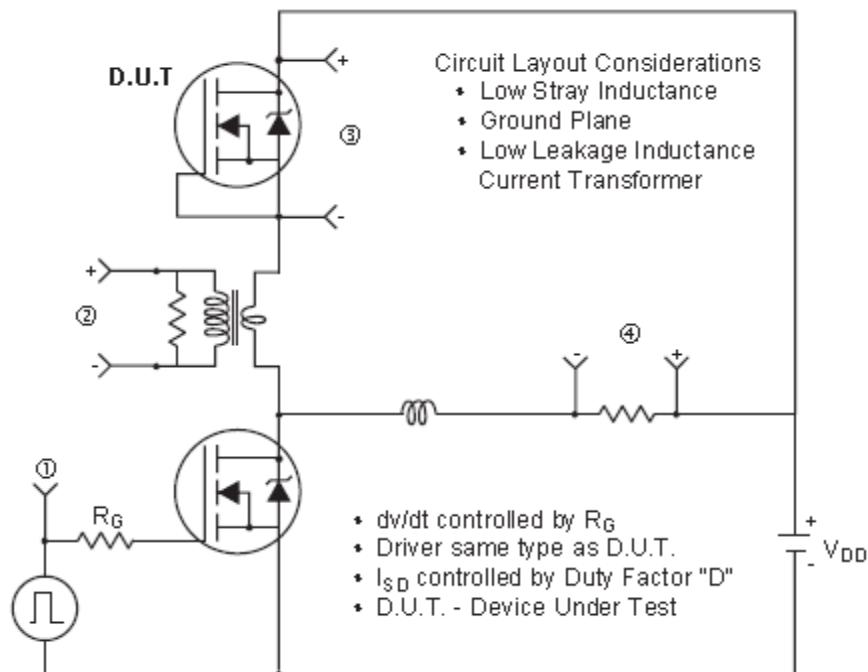


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



* $V_{GS} = 5V$ for Logic Level Devices

Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

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